



PD60004 PD60004S

RF POWER TRANSISTORS *The LdmoST Plastic FAMILY*

TARGET DATA

Designed for GSM / EDGE / IS-97 applications

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 4\text{ W}$ with 11 dB gain @ 2000 MHz

DESCRIPTION

The PD60004 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 26 V in common source mode at frequencies of up to 2 GHz. PD60004 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF. PD60004's superior linearity performance makes it an ideal solution for base station applications.

The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.

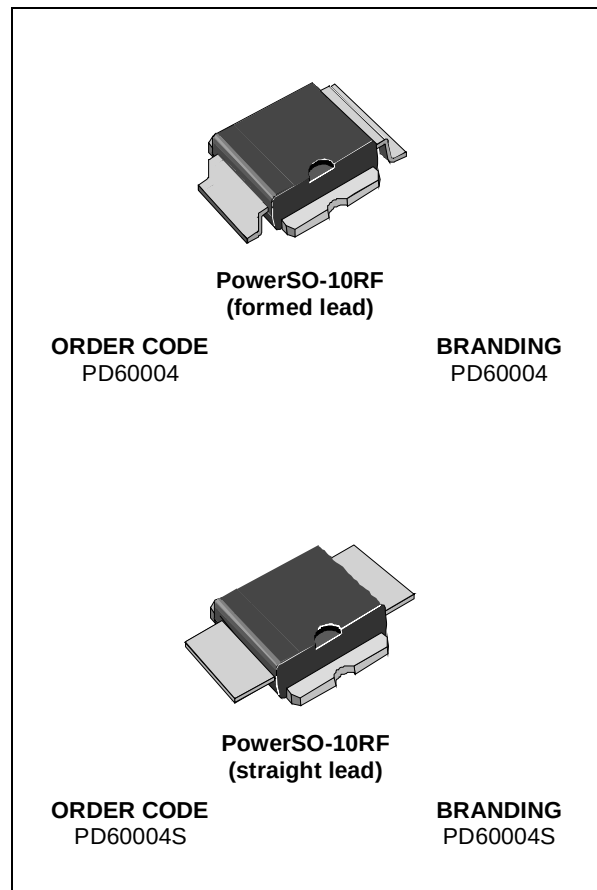
Mounting recommendations are available in www.st.com/rfl (look for application note AN1294)

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25\text{ }^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Voltage	65	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	TBD	A
P_{DISS}	Power Dissipation (@ $T_c = 70^{\circ}\text{C}$)	TBD	W
T_j	Max. Operating Junction Temperature	165	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to +175	$^{\circ}\text{C}$

THERMAL DATA ($T_{CASE} = 70\text{ }^{\circ}\text{C}$)

$R_{th(j-c)}$	Junction -Case Thermal Resistance	TBD	$^{\circ}\text{C/W}$
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PD60004 - PD60004S

ELECTRICAL SPECIFICATION (T_{CASE} = 25°C)

STATIC

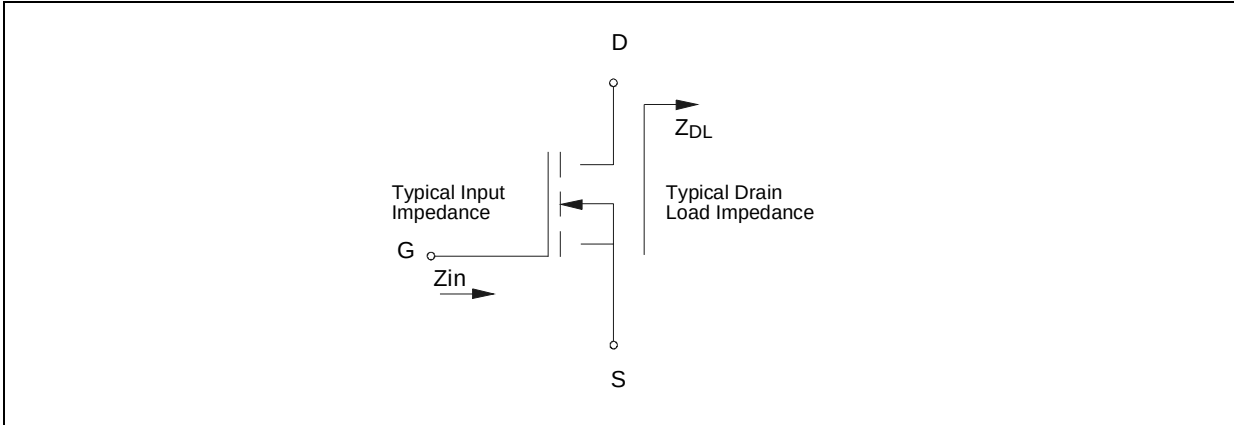
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	I _{DS} = 1 mA	65			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 28 V			1	μA
I _{GSS}	V _{GS} = 20 V	V _{DS} = 0 V			1	μA
V _{GS(Q)}	V _{DS} = 28 V	I _D = 35 mA	2.5		5.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 0.3 A		TBD		V
G _{FS}	V _{DS} = 10 V	I _D = 0.3 A	2.0	TBD		mho
C _{ISS}	V _{GS} = 0 V	V _{DS} = 28 V	f = 1 MHz		TBD	pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 28 V	f = 1 MHz		TBD	pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 28 V	f = 1 MHz		TBD	pF

DYNAMIC

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
P _{out}	V _{DD} = 26 V	I _{DQ} = 35 mA	f = 2000 MHz	4			W
IMD3	V _{DD} = 26 V	I _{DQ} = 35 mA	P _{OUT} = 4 W PEP		-32	-28	dBc
G _{PS}	V _{DD} = 26 V	I _{DQ} = 35 mA	P _{OUT} = 4 W PEP	11	12		dB
η _D	V _{DD} = 26 V	I _{DQ} = 35 mA	P _{OUT} = 4 W PEP		35		%
Load mismatch	V _{DD} = 26 V	I _{DQ} = 35 mA	P _{OUT} = 4 W ALL PHASE ANGLES	10:1			VSWR

note: f₁ = 2000 MHz
PEP f₂ = 2000.1 MHz

IMPEDANCE DATA

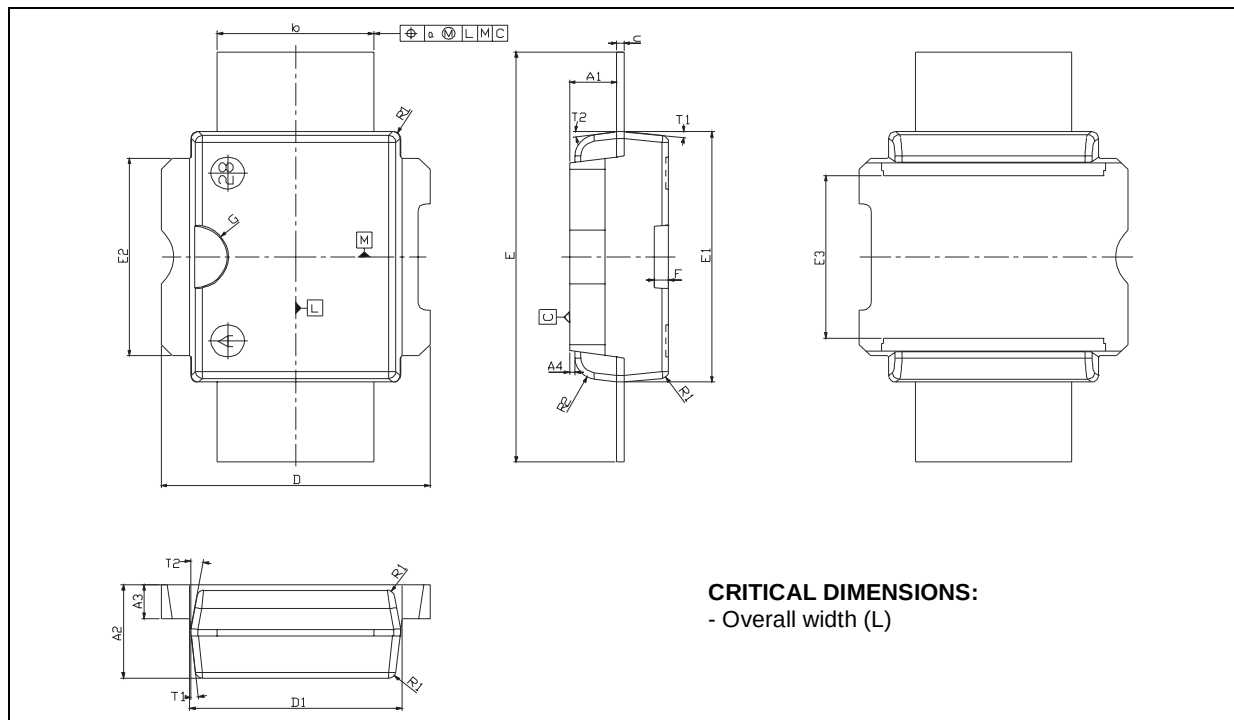


FREQ. MHz	Z _{IN} (Ω)	Z _{DL} (Ω)
1800		
1850		
1900		
1950		
2000		

PowerSO-10RF Straight Lead MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A1	1.62	1.67	1.72	0.064	0.065	0.068
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	15.15	15.4	15.65	0.595	0.606	0.615
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
R1			0.25			0.01
R2		0.8			0.031	
T1		6 deg			6 deg	
T2		10 deg			10 deg	

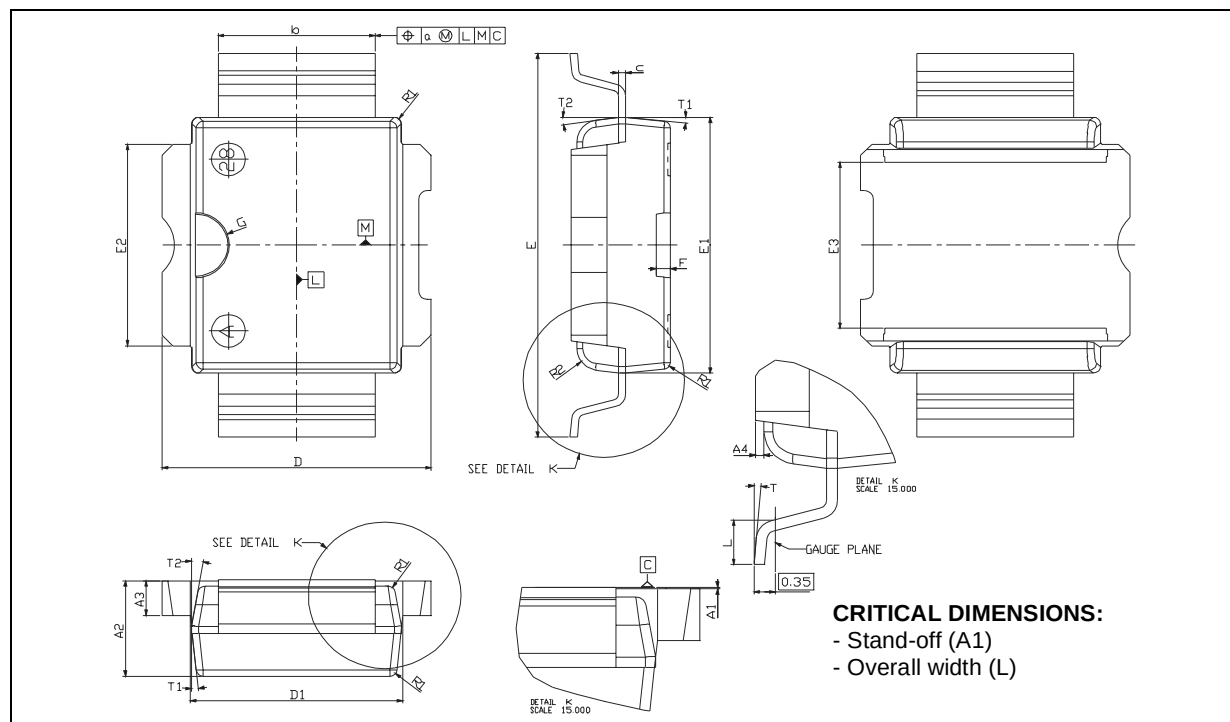
Note (1): Resin protrusions not included (max value: 0.15 mm per side)



PowerSO-10RF Formed Lead (Gull Wing) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A1	0	0.05	0.1	0.	0.0019	0.0038
A2	3.4	3.5	3.6	0.134	0.137	0.142
A3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
a		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
c	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	13.85	14.1	14.35	0.544	0.555	0.565
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
L	0.8	1	1.1	0.030	0.039	0.042
R1			0.25			0.01
R2		0.8			0.031	
T	2 deg	5 deg	8 deg	2 deg	5 deg	8 deg
T1		6 deg			6 deg	
T2		10 deg			10 deg	

Note (1): Resin protrusions not included (max value: 0.15 mm per side)



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